L Number	Hits	Search Text	DB	Time stamp
1	2458398	chip die dice ic (integrated adj circuit) semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/03/04 08:50
2	253072	(plurality stack stacked stacking multi multiple) with (chip die dice ic (integrated adj circuit) semiconductor)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/03/04 10:58
3	18493	wire same ((plurality stack stacked stacking multi multiple) with (chip die dice ic (integrated adj circuit) semiconductor))	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/03/04 08:54
4	831653	control and memory znc (wire same ((plurality stack stacked stacking multi multiple) with (chip die dice ic (integrated adj circuit) semiconductor)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/03/04 08:55
5	2561	control and memory and (wire same ((plurality stack stacked stacking multi multiple) with (chip die dice ic (integrated adj circuit) semiconductor)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/03/04 10:53
6	1597	<pre>(lead leadframe (lead adj frame)) and (control and memory and (wire same ((plurality stack stacked stacking multi multiple) with (chip die dice ic (integrated adj circuit) semiconductor))))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 10:51
7	1466	<pre>((lead leadframe (lead adj frame)) and (control and memory and (wire same ((plurality stack stacked stacking multi multiple) with (chip die dice ic (integrated adj circuit) semiconductor))))) and (pad terminal electrode)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 10:52
8	10507	(lead leadframe (lead adj frame)) and (wire same ((plurality stack stacked stacking multi multiple) with (chip die dice ic (integrated adj circuit) semiconductor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/03/04 10:52
9	9142	((lead leadframe (lead adj frame)) and (wire same ((plurality stack stacked stacking multi multiple) with (chip die dice ic (integrated adj circuit) semiconductor)))) and (pad terminal electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 10:52
10	7676	<pre>(((lead leadframe (lead adj frame)) and (wire same ((plurality stack stacked stacking multi multiple) with (chip die dice ic (integrated adj circuit) semiconductor)))) and (pad terminal electrode)) not (((lead leadframe (lead adj frame)) and (control and memory and (wire same ((plurality stack stacked stacking multi multiple) with (chip die dice ic (integrated adj circuit) semiconductor))))) and (pad terminal electrode))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 10:52

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11	3254	(control memory nonvolatile (non adj	USPAT;	2004/03/04
111	3234	volatile) and (((lead leadframe (lead	US-PGPUB;	10:57
		adj frame)) and (wire same ((plurality	EPO; JPO;	10.37
İ		stack stacked stacking multi multiple)	DERWENT;	
		with (chip die dice ic (integrated adj	IBM TDB	
1		circuit) semiconductor)))) and (pad	1511_155	
		terminal electrode)) not (((lead	·	
		leadframe (lead adj frame)) and (control		
		and memory and (wire same ((plurality		
		stack stacked stacking multi multiple)		
		with (chip die dice ic (integrated adj		
		circuit) semiconductor))))) and (pad		
		terminal electrode)))		
12	1090	(stack stacked stacking) and ((control	USPAT;	2004/03/04
		memory nonvolatile (non adj volatile))	US-PGPUB;	10:59
		and ((((lead leadframe (lead adj frame))	EPO; JPO;	
		and (wire same ((plurality stack stacked	DERWENT;	
	i	stacking multi multiple) with (chip die	IBM_TDB	
]		dice ic (integrated adj circuit)		
		semiconductor)))) and (pad terminal		
		electrode)) not (((lead leadframe (lead		i
		adj frame)) and (control and memory and		-
		(wire same ((plurality stack stacked		
		stacking multi multiple) with (chip die dice ic (integrated adj circuit)		
		semiconductor))))) and (pad terminal		
		electrode))))		

L	Hits	Search Text	DB	Time stamp
Number				
1	2458398	chip die dice ic (integrated adj circuit)	USPAT;	2004/03/04
		semiconductor	US-PGPUB;	08:50
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
2	253072	/ml.,mality.ot-ale_starle_starle_starleing_starleing_starleing	USPAT;	2004/02/04
2	253072			2004/03/04
		multiple) with (chip die dice ic	US-PGPUB;	08:52
		(integrated adj circuit) semiconductor)	EPO; JPO;	
			DERWENT;	
	1		IBM_TDB	
3	18493		USPAT;	2004/03/04
		stacking multi multiple) with (chip die	US-PGPUB;	08:54
	1	dice ic (integrated adj circuit)	EPO; JPO;	1
		semiconductor))	DERWENT;	`
		, ,	IBM TDB	
4	831653	control and memory znc (wire same	USPAT;	2004/03/04
•	002000	((plurality stack stacked stacking multi	US-PGPUB;	08:55
		multiple) with (chip die dice ic	EPO; JPO;	00.55
		(integrated adj circuit) semiconductor)))	, ,	
		(Integrated adj Circuit) Semiconductor,,,	DERWENT;	
5	05.61		IBM_TDB	2004/20/20
5	2561	control and memory and (wire same	USPAT;	2004/03/04
		((plurality stack stacked stacking multi	US-PGPUB;	08:55
		multiple) with (chip die dice ic	EPO; JPO;	
		(integrated adj circuit) semiconductor)))	DERWENT;	
			IBM TDB	
6	1597	(lead leadframe (lead adj frame)) and	USPĀT;	2004/03/04
		(control and memory and (wire same	US-PGPUB;	08:56
		((plurality stack stacked stacking multi	EPO; JPO;	
		multiple) with (chip die dice ic	DERWENT;	
		(integrated adj circuit)	IBM TDB	
		semiconductor))))	1201-122	
7	1466		USPAT;	2004/03/04
′	1400			1
	1	(control and memory and (wire same	US-PGPUB;	08:57
	1	((plurality stack stacked stacking multi	EPO; JPO;]
		multiple) with (chip die dice ic	DERWENT;	
	1	(integrated adj circuit)	IBM_TDB	
		semiconductor))))) and (pad terminal		
		electrode)		